

AMENDMENTS TO THE CLAIMS

1. (original) A method of forming an interconnect line in an integrated circuit, the method comprising:
 - depositing a sacrificial layer overlying a metallization level;
 - forming an opening in the sacrificial layer;
 - depositing a metal in the opening, the metal being coupled to an interconnect line in the metallization level; and
 - etching the sacrificial layer using a chemistry that includes a noble gas fluoride to create an air core overlying the metallization level.
2. (original) The method of claim 1 further comprising the act of planarizing the metal prior to exposing the sacrificial layer.
3. (original) The method of claim 1 further comprising the act of depositing a topside layer overlying the air core.
4. (original) The method of claim 1 further comprising the act of depositing a capping layer overlying the sacrificial layer prior to forming an opening in the sacrificial layer.
5. (original) The method of claim 1 wherein the sacrificial layer is deposited overlying a support layer.
6. (original) The method of claim 1 wherein the opening includes a via.
7. (original) The method of claim 1 wherein the metal includes copper.
8. (original) The method of claim 1 wherein the noble gas fluoride includes xenon difluoride.
9. (original) The method of claim 1 wherein the sacrificial layer includes polycrystalline silicon.
10. (original) The method of claim 4 wherein the capping layer includes silicon nitride.
11. (original) The method of claim 1 wherein the metallization level includes a damascene structure.
- 12-20 (canceled)